



UTG80N65ND-S

Preliminary

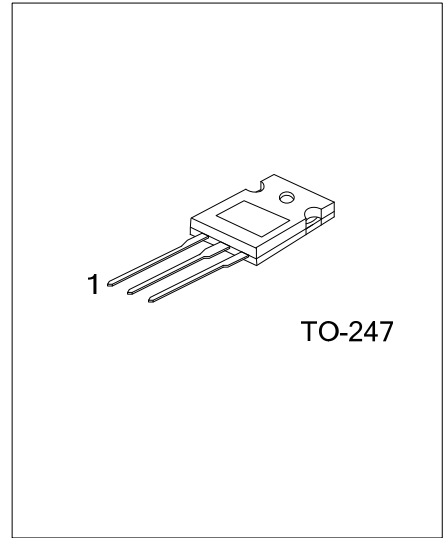
Insulated Gate Bipolar Transistor

650V TRENCH GATE FIELD-STOP IGBT

DESCRIPTION

The UTC **UTG80N65ND-S** is an Trench Field-Stop Insulated Gate Bipolar Transistor. it uses UTC's advanced technology to provide customers with high switching speed, low saturation voltage and low switching loss, etc.

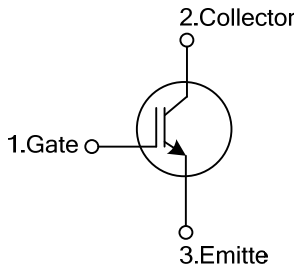
The UTC **UTG80N65ND-S** is suitable for the resonant or soft switching applications.



FEATURES

- * High switching speed
- * High avalanche ruggedness
- * Low saturation voltage: $V_{CE(SAT),Typ.} = 1.6V @ I_C=80A, V_{GE}=15V$ ($T_C = 25^\circ C$)

SYMBOL



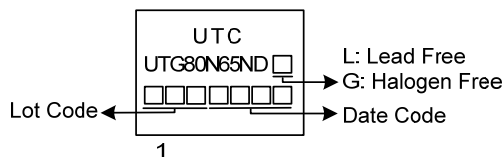
ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
UTG80N65NDL-T47-T	UTG80N65NDG-T47-T	TO-247	G	C	E	Tube

Note: Pin Assignment: G: Gate C: Collector E: Emitter

<p>UTG80N65NDG-T47-T</p> <p>(1)Packing Type</p> <p>(2)Package Type</p> <p>(3)Green Package</p>	<p>(1) T: Tube</p> <p>(2) T47: TO-247</p> <p>(3) G: Halogen Free and Lead Free, L: Lead Free</p>
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MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_A=25°C, unless otherwise noted)

PARAMETER	SYMBOL	RATINGS	UNIT
Collector-Emitter Voltage	V _{CE}	650	V
Gate-Emitter Voltage	V _{GE}	±20	V
Transient Gate-emitter voltage (t _p < 5 ms)		±25	V
Continuous Collector Current	I _C	T _C =25°C	160
		T _C =100°C	80
Collector Current Pulsed (Note 1)	I _{CM}	320	A
Short Circuit Withstand Time V _{GE} = 15V, V _{CC} ≤ 200V Allowed number of short circuits < 1000 Time between short circuits: ≥1.0s T _{VJ} = 25°C	t _{sc}	10	μs
Power Dissipation (T _C =25°C)	P _D	285	W
Operating Junction Temperature	T _J	-40 ~ +175	°C
Storage Temperature Range	T _{STG}	-55 ~ +175	°C

Notes: 1. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

Absolute maximum ratings are those values beyond which the device could be permanently damaged.

2. Pulse width limited by maximum junction temperature.

■ THERMAL DATA

PARAMETER	SYMBOL	RATING	UNIT
Junction to Case	θ _{JC}	0.44	°C/W

■ ELECTRICAL CHARACTERISTICS (T_C=25°C, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Off Characteristics						
Collector-Emitter Breakdown Voltage	BV _{CE}		650			V
Collector Cut-Off Current	I _{CES}	V _{CE} =650V, V _{GE} =0V			5	μA
G-E Leakage Current	I _{GES}	V _{CE} =0V, V _{GE} =±20V			±400	nA
On Characteristics						
Gate to Emitter Threshold Voltage	V _{GE(TH)}	I _C =250μA, V _{CE} =V _{GE}	4.5		6.5	V
Collector to Emitter Saturation Voltage	V _{CE(SAT)}	I _C =80A, V _{GE} =15V	T _C =25°C	1.6	2.1	V
			T _C =125°C	1.8		V
Dynamic Characteristics						
Input Capacitance	C _{IES}	V _{CE} =25V, V _{GE} =0V, f=1MHz		5270		pF
Output Capacitance	C _{OES}			280		pF
Reverse Transfer Capacitance	C _{RES}			84		pF
Switching Characteristics						
Total Gate Charge	Q _G	V _{CE} =520V, I _C =80A, V _{GE} =15V		221		nC
Gate-Emitter Charge	Q _{GE}			45		nC
Gate-Collector Charge	Q _{GC}			96		nC
Turn-On Delay Time	t _{DON}	V _{CC} =400V, I _C =80A, R _G =5Ω, V _{GE} =0~15V, L=500μH		32		ns
Rise Time	t _R			89		ns
Turn-Off Delay Time	t _{DOFF}			176		ns
Fall Time	t _F			50		ns
Turn-On Switching Loss	E _{ON}			4.15		mJ
Turn-Off Switching Loss	E _{OFF}			2.94		mJ

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